

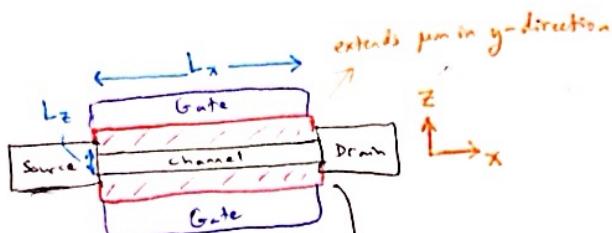
## Lecture #5

### Quantization Effects

#### • Subbands

In a homogeneous solid (3D), electrons are free to move in all three directions and energy levels are classified:  $E_b(k_x, k_y, k_z)$   
 bands, such as valence or conduction

What happens in this device?



Channel is a quantum well with  $e^-$ s free to move only in  $x-y$  plane

$z$ -confinement modeled as a ring of circumference  $L_z$ , with periodic B.C. that restrict to allowed values of  $K_z$  given by:  $K_z = \frac{p2\pi}{L_z}$

For a ring-shaped wire or nanotube this would be

$$E_{b,p}(k_x, k_y) \approx E_b(k_x, k_y, K_z = \frac{p2\pi}{L_z})$$

$p \equiv$  subband index,  $1, 2, 3, \dots$

The energy levels are now classified as:

$$E_{b,p}(k_x, k_y) \approx E_b(k_x, k_y, K_z = \frac{p2\pi}{L_z})$$

for the structure shown above,  
where the insulator layers act like  $\infty$  potential wells

This is an approximation, but shows the following critical points

★ Quantum wells have 1D subbands, each having a 2D dispersion relation,  $E(k_x, k_y)$ .

\* How small does  $L_z$  need to be for something to be a 2D (quantum well)?

A: When it has experimentally observable effects.

→ Typically, the discrete energy levels of  $K_z = \frac{p\pi}{L_z}$  need to be  $> k_B T$  (thermal energy)

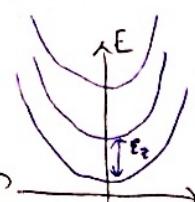
Due to smoothing out of Fermi function

Example with parabolic  $E-K$ :

$$E(\vec{k}) \approx E_c + \frac{\hbar^2(k_x^2 + k_y^2)}{2m_e}$$

Conduction band edge

effective mass in conduction band



confinement in  $z$  gives rise to subbands:

$$E_p(k_x, k_y) \approx E_c + p^2 \epsilon_z + \frac{\hbar^2(k_x^2 + k_y^2)}{2m_e}$$

where:  $\epsilon_z = \frac{\hbar^2 \pi^2}{2m_e L_z^2} = \frac{m_0}{m_e} \left( \frac{10 \text{ nm}}{L_z} \right)^2 \times 3.8 \text{ meV}$

## Lecture # 5 (CONT)

### Quantization Effects (CONT)

#### • Subbands (CONT)

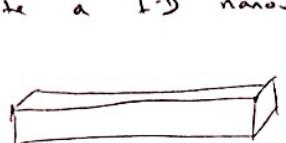
Example: Si, ETSOI : when is it 2D? [IN class exercise]

However  $m_c = 0.2 m_0$ ,  $k_B T \approx 26 \text{ meV} @ R.T.$

$$\therefore \frac{1}{0.2} \left( \frac{10 \text{ nm}}{L_z} \right)^2 (3.8 \text{ meV}) > 26 \text{ meV}$$

$$\frac{1900 \text{ nm}}{L_z^2} > 26 \Rightarrow L_z < 8.5 \text{ nm}$$

OK, now what happens if we confine our channel in the y-direction as well to create a 1-D nanowire structure? Also called "quantum wires"



$$E_{n,p}(k_x) \approx E_c + n^2 \epsilon_y + p^2 \epsilon_z + \frac{\hbar^2 k_x^2}{2m_c}$$

$$\epsilon_y = \frac{\hbar^2 \pi^2}{2L_y^2}$$

\* Quantum wires (1D) have 2D subbands, each having a 1-D dispersion relation

#### • Density of States

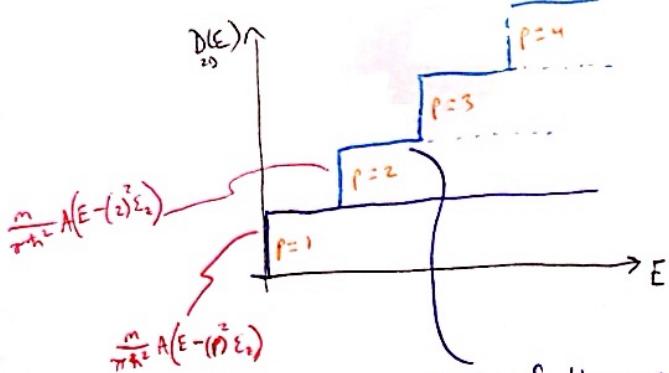
From Lecture #1 we found the 3D-Dos:  $D_{3D}(E) = \frac{m \sqrt{2mE}}{\pi^2 \hbar^3} V$  (includes spin)

Following the same approach for 2D gives:  $D_{2D}(E) = \frac{m}{\pi \hbar^2 A}$

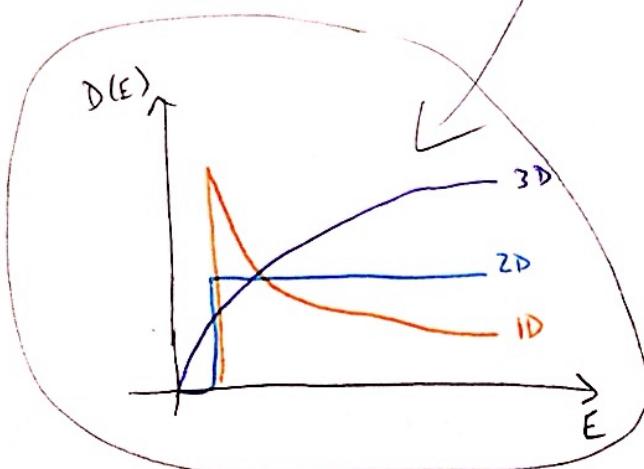
for 1D:  $D_{1D}(E) = \frac{m}{\pi \hbar} (2mE)^{1/2} \cdot L$

HOWEVER, the  $D_{2D}$  and  $D_{1D}$  are for only one subband! Must sum over all subbands:

$$D_{2D}(E) = \frac{m}{\pi \hbar^2 A} \sum_p \delta(E - p^2 \epsilon_z)$$



each of these subbands  
is called a "mode" for  
carrier transport



## Lecture # 5 (cont)

Back to  $G_a$

What is conductance of a material that is 1D, with perfect contacts?

Before, we said:  $G_a = \frac{2e^2}{h}$

Now, to consider the entire electronic structure:

$$G = \underbrace{M(E)}_{\text{# of modes at } E} G_a$$